ABSTRACT

SEMICONDUCTOR MEMORY DEVICE AND MANUFACTURING METHOD OF SEMICONDUCTOR MEMORY DEVICE

There are provided a semiconductor memory device and a manufacturing method of the same. The semiconductor memory device includes: a stack structure including conductive patterns and interlayer insulating layers, which are alternately stacked in a first direction; a channel layer penetrating the stack structure; a first semiconductor layer disposed on the stack structure, the first semiconductor layer including a first impurity of a first conductivity type; a second semiconductor layer disposed on the first semiconductor layer, the second semiconductor layer including a well region with a second impurity of a second conductivity type, wherein the second conductivity type is different from the first conductivity type; and a memory layer between the channel layer and the stack structure.

FIG. 4